

STAC4932B

Datasheet - production data

HF/VHF/UHF RF power N-channel MOSFET

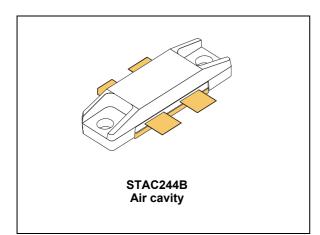
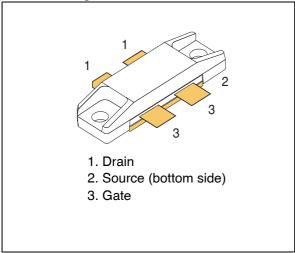


Figure 1. Pin connection



Features

- Excellent thermal stability
- Common source push-pull configuration
- P_{OUT} = 1000 W min. (1200 W typ.) with 26 dB gain @ 123 MHz
- Pulse conditions: 1 msec 10%
- In compliance with the 2002/95/EC European directive
- ST air-cavity STAC[®] packaging technology

Description

The STAC4932B is an N-channel MOS field-effect RF power transistor. It is intended for 100 V pulse applications up to 250 MHz. This device is suitable for use in industrial, scientific and medical applications. The STAC4932B benefits from the latest generation of efficient, patent-pending STAC[®] package technology.

Table 1. Device summary

Order code	Marking	Package	Packaging
STAC4932B	STAC4932 ⁽¹⁾	STAC244B	Plastic tray

1. For more details please refer to Chapter 6: Marking, packing and shipping specifications.

Contents

1	Electrical data
	1.1 Maximum ratings 3
	1.2 Thermal data
2	Electrical characteristics
	2.1 Static
	2.2 Dynamic
3	Impedance
4	Typical performance6
5	Package mechanical data 9
6	Marking, packing and shipping specifications
7	Revision history



1 Electrical data

1.1 Maximum ratings

Symbol	Parameter	Value	Unit		
V _{(BR)DSS} ⁽¹⁾	Drain source voltage	200	V		
V _{DGR}	Drain-gate voltage (R_{GS} = 1 M Ω)	200	V		
V _{GS}	Gate-source voltage	±20	V		
Τ _J	Max. operating junction temperature	200	°C		
T _{STG}	Storage temperature	-65 to +150	°C		
T - 150 °C	•		•		

Table 2. Absolute maximum ratings (T_{CASE} = 25 °C)

1. T_J = 150 °C

1.2 Thermal data

Table 3. Thermal data (1 msec - 10%)

Symbol	Parameter	Value	Unit
R _{thJC}	Junction - case thermal resistance	0.075	°C/W



2 Electrical characteristics

T_{CASE} = +25 °C

2.1 Static

Table 4. Static (per side)						
	Test conditions		Min.	Тур.	Max.	Unit
V _{GS} = 0 V	I _{DS} = 100 mA		200	250		V
V _{GS} = 0 V	V _{DS} = 100 V				1	mA
V _{GS} = 20 V	V _{DS} = 0 V				250	nA
I _D = 250 mA			2.0		4.0	V
V _{GS} = 10 V	I _D = 10 A				3.6	V
V _{DS} = 10 V	I _D = 2.5 A			6		S
V_{GS} = 0 V	V _{DS} = 100 V	f = 1 MHz		570		pF
V_{GS} = 0 V	V _{DS} = 100 V	f = 1 MHz		134		pF
V _{GS} = 0 V	V _{DS} = 100 V	f = 1 MHz		8		pF
	$V_{GS} = 0 V$ $V_{GS} = 20 V$ $I_{D} = 250 mA$ $V_{GS} = 10 V$ $V_{DS} = 10 V$ $V_{GS} = 0 V$ $V_{GS} = 0 V$	$\begin{tabular}{ c c c c } \hline Test \ conditions \\ \hline V_{GS} = 0 \ V & I_{DS} = 100 \ mA \\ \hline V_{GS} = 0 \ V & V_{DS} = 100 \ V \\ \hline V_{GS} = 20 \ V & V_{DS} = 0 \ V \\ \hline I_D = 250 \ mA \\ \hline V_{GS} = 10 \ V & I_D = 10 \ A \\ \hline V_{DS} = 10 \ V & I_D = 2.5 \ A \\ \hline V_{GS} = 0 \ V & V_{DS} = 100 \ V \\ \hline V_{GS} = 0 \ V & V_{DS} = 100 \ V \\ \hline \end{array}$	Test conditions $V_{GS} = 0 V$ $I_{DS} = 100 \text{ mA}$ $V_{GS} = 0 V$ $V_{DS} = 100 V$ $V_{GS} = 20 V$ $V_{DS} = 0 V$ $I_D = 250 \text{ mA}$ $V_{GS} = 10 V$ $V_{GS} = 10 V$ $I_D = 10 \text{ A}$ $V_{DS} = 10 V$ $I_D = 2.5 \text{ A}$ $V_{GS} = 0 V$ $V_{DS} = 100 V$ $f = 1 \text{ MHz}$ $V_{GS} = 0 V$ $V_{DS} = 100 V$ $f = 1 \text{ MHz}$	Test conditions Min. $V_{GS} = 0 \vee$ $I_{DS} = 100 \text{ mA}$ 200 $V_{GS} = 0 \vee$ $V_{DS} = 100 \vee$ 200 $V_{GS} = 20 \vee$ $V_{DS} = 100 \vee$ 200 $V_{GS} = 20 \vee$ $V_{DS} = 0 \vee$ 200 $I_D = 250 \text{ mA}$ 2.0 $V_{GS} = 10 \vee$ $I_D = 10 \text{ A}$ 2.0 $V_{DS} = 10 \vee$ $I_D = 2.5 \text{ A}$ 2.0 $V_{GS} = 0 \vee$ $V_{DS} = 100 \vee$ $f = 1 \text{ MHz}$ $V_{GS} = 0 \vee$ $V_{DS} = 100 \vee$ $f = 1 \text{ MHz}$	Test conditions Min. Typ. $V_{GS} = 0 \vee$ $I_{DS} = 100 \text{ mA}$ 200 250 $V_{GS} = 0 \vee$ $V_{DS} = 100 \vee$ 1 1 $V_{GS} = 20 \vee$ $V_{DS} = 100 \vee$ 1 1 $V_{GS} = 20 \vee$ $V_{DS} = 0 \vee$ 2.0 1 $I_D = 250 \text{ mA}$ 2.0 2.0 1 $V_{GS} = 10 \vee$ $I_D = 10 \text{ A}$ 2.0 1 $V_{DS} = 10 \vee$ $I_D = 2.5 \text{ A}$ 6 6 $V_{GS} = 0 \vee$ $V_{DS} = 100 \vee$ f = 1 MHz 570 $V_{GS} = 0 \vee$ $V_{DS} = 100 \vee$ f = 1 MHz 134	Test conditions Min. Typ. Max. $V_{GS} = 0 \vee$ $I_{DS} = 100 \text{ mA}$ 200 250 $V_{GS} = 0 \vee$ $V_{DS} = 100 \vee$ 1 1 $V_{GS} = 20 \vee$ $V_{DS} = 0 \vee$ 250 250 $I_D = 250 \text{ mA}$ 2.0 4.0 250 $V_{GS} = 10 \vee$ $I_D = 10 \text{ A}$ 3.6 3.6 $V_{DS} = 10 \vee$ $I_D = 2.5 \text{ A}$ 6 6 $V_{GS} = 0 \vee$ $V_{DS} = 100 \vee$ f = 1 MHz 570 $V_{GS} = 0 \vee$ $V_{DS} = 100 \vee$ f = 1 MHz 134

Table 4. Static (per side)

1. T_J = 150 °C

2.2 Dynamic

Symbol	Test conditions		Тур.	Max.	Unit
P _{OUT}	V _{DD} = 100 V, I _{DQ} = 2 x 250 mA, f = 123 MHz	1000	1200	-	W
h _D	V _{DD} = 100 V, I _{DQ} = 2 x 250 mA, P _{OUT} = 1000 W, f = 123 MHz		60	-	%
Gain	V _{DD} = 100 V, I _{DQ} = 2 x 250 mA, P _{OUT} = 1000 W, f = 123 MHz		26	-	dB

Table 5. Pulse / 1 msec - 10%



3 Impedance

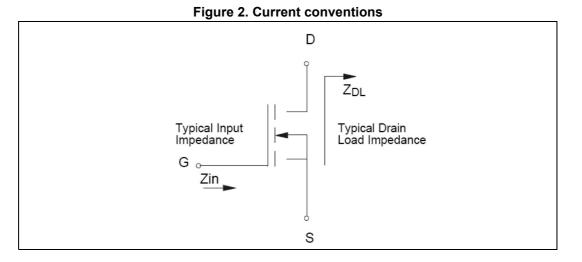


Table 6. Impedance data

Freq. (MHz)	Z _{IN} (Ω) Z _{DL} (Ω)	
123 MHz (pulsed)	1.3 - j 2.8	7.7 - j 9.4

Note: Measured gate-to-gate and drain-to-drain, respectively.



4 Typical performance

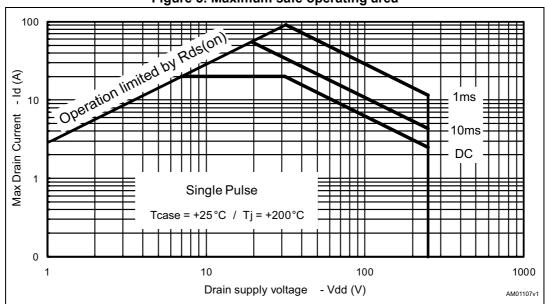
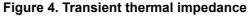
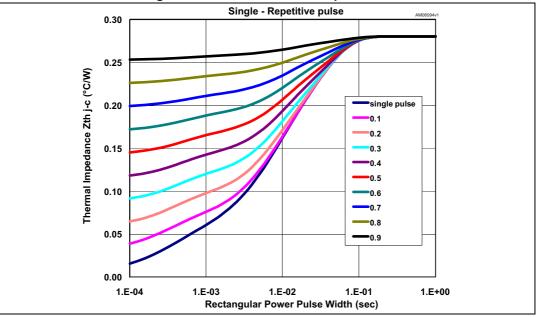


Figure 3. Maximum safe operating area







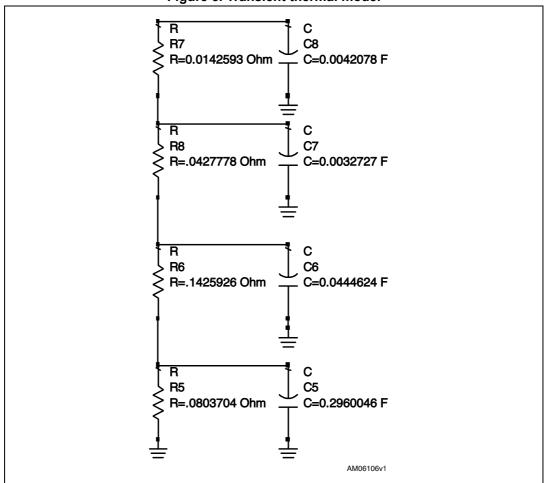
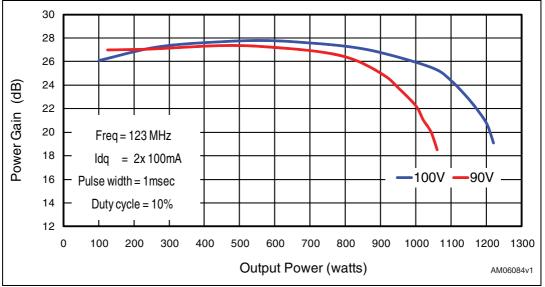


Figure 5. Transient thermal model







DocID17153 Rev 6

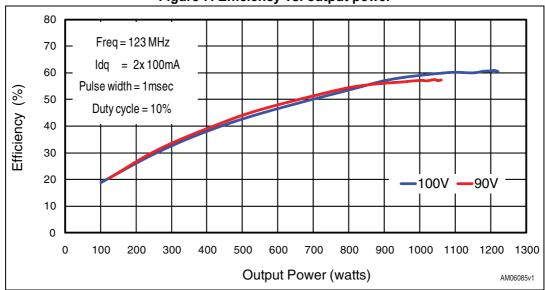


Figure 7. Efficiency vs. output power



5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Dim.		mm	
Dini.	Min.	Тур.	Max.
A	5.08		5.59
A1	4.32		4.83
В	4.32		5.33
С	9.65		9.91
D	17.78		18.08
E	33.88		34.19
F	0.10		0.15
G		1.02	
Н	1.45		1.70
I	4.83		5.33
J	9.27		9.52
К	27.69		28.19
L	3.12	3.23	3.33
М	3.35	3.45	3.56

Table 7. STAC244B mechanical data



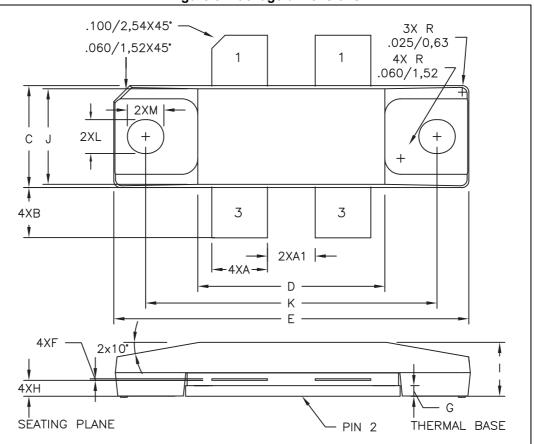


Figure 8. Package dimensions



6 Marking, packing and shipping specifications

Order code	Packaging	Pcs per tray	Dry pack humidity	Lot code
STAC4932B	Tray	20	< 10%	Not mixed

Figure 9. Marking layout

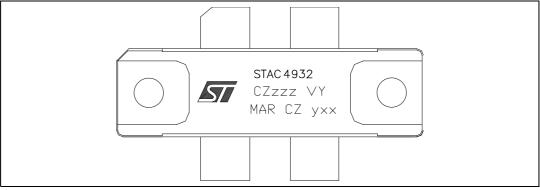


Table 9. Marking specifications

Symbol	Description	
CZ	Assembly plant	
ZZZ	Last 3 digits of diffusion lot	
VY	Diffusion plant	
MAR	Country of origin	
CZ	Test and finishing plant	
У	Assembly year	
ХХ	Assembly week	



7 Revision history

Date	Revision	Changes	
19-Feb-2010	1	First release.	
26-May-2010	2	Document status promoted from preliminary data to datasheet.	
03-Aug-2010	3	Updated description on cover page and Table 3.	
03-Sep-2010	4	Updated figures: 3, 4 and 5.	
12-Sep-2011	5	Inserted new Section 6: Marking, packing and shipping specifications. Updated Table 6. Minor text changes.	
01-Jul-2013	6	Modified pin labeling in <i>Figure 1: Pin connection</i> . Modified document title. Minor text corrections throughout document.	

Table 10. Document revision history



Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

ST PRODUCTS ARE NOT AUTHORIZED FOR USE IN WEAPONS. NOR ARE ST PRODUCTS DESIGNED OR AUTHORIZED FOR USE IN: (A) SAFETY CRITICAL APPLICATIONS SUCH AS LIFE SUPPORTING, ACTIVE IMPLANTED DEVICES OR SYSTEMS WITH PRODUCT FUNCTIONAL SAFETY REQUIREMENTS; (B) AERONAUTIC APPLICATIONS; (C) AUTOMOTIVE APPLICATIONS OR ENVIRONMENTS, AND/OR (D) AEROSPACE APPLICATIONS OR ENVIRONMENTS. WHERE ST PRODUCTS ARE NOT DESIGNED FOR SUCH USE, THE PURCHASER SHALL USE PRODUCTS AT PURCHASER'S SOLE RISK, EVEN IF ST HAS BEEN INFORMED IN WRITING OF SUCH USAGE, UNLESS A PRODUCT IS EXPRESSLY DESIGNATED BY ST AS BEING INTENDED FOR "AUTOMOTIVE, AUTOMOTIVE SAFETY OR MEDICAL" INDUSTRY DOMAINS ACCORDING TO ST PRODUCT DESIGN SPECIFICATIONS. PRODUCTS FORMALLY ESCC, QML OR JAN QUALIFIED ARE DEEMED SUITABLE FOR USE IN AEROSPACE BY THE CORRESPONDING GOVERNMENTAL AGENCY.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2013 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com



DocID17153 Rev 6